## **SPTECH Silicon PNP Power Transistor**

### 2SA1758



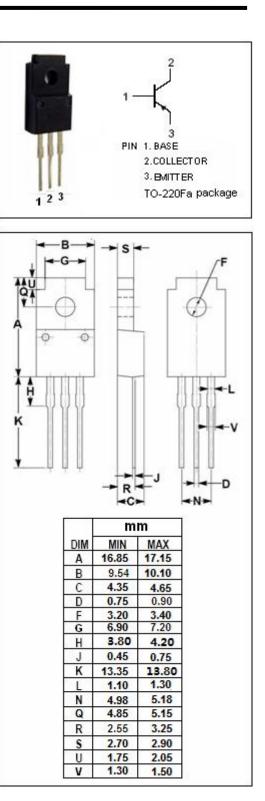
- Collector-Emitter Breakdown Voltage : V<sub>(BR)CEO</sub>= -60V(Min)
- DC Current Gain-
- : h<sub>FE</sub>= 60(Min)@ (V<sub>CE</sub>= -2V, I<sub>C</sub>= -2A)
- · Low Saturation Voltage-
  - :  $V_{CE(sat)}$  = -0.3V(Max)@ (I<sub>C</sub>= -6A, I<sub>B</sub>= -0.3A)

#### **APPLICATIONS**

• Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)						
SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>CBO</sub>	Collector-Base Voltage	-100	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V			
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V			
lc	Collector Current-Continuous	-12	А			
Pc	Collector Power Dissipation @T <sub>c</sub> =25°C	30	W			
TJ	Junction Temperature	150	°C			
T <sub>stg</sub>	Storage Temperature	-55~150	°C			

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)



## **SPTECH Silicon PNP Power Transistor**

## 2SA1758

#### **ELECTRICAL CHARACTERISTICS**

#### Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA ; I <sub>B</sub> = 0	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -50 μ A ; I <sub>C</sub> = 0	-5			v
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.3A			-0.3	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -8A; I <sub>B</sub> = -0.4A			-0.5	V
V <sub>BE(sat)-1</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.3A			-1.2	V
V <sub>BE(sat)-2</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -8A; I <sub>B</sub> = -0.4A			-1.5	v
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V ; I <sub>E</sub> =0			-10	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> =0			-10	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= -1A ; Vce= -2V	100			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -2A ; V <sub>CE</sub> = -2V	60		320	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A ; V <sub>CE</sub> = -10V		90		MHz

#### • h<sub>FE-2</sub> Classifications

D	Е	F
60-120	100-200	160-320

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by SPTECH manufacturer:

Other Similar products are found below :

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B